

## Features

- Surface Mount Package
- Glass Passivated Diode Construction
- Moisture Resistant Epoxy Case
- High Surge Current Capability

## Maximum Ratings

- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C

MCC Catalog Number	Device Marking	Maximum Rccurent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MB05S	MB05S	50V	35V	50V
MB1S	MB1S	100V	70V	100V
MB2S	MB2S	200V	140V	200V
MB4S	MB4S	400V	280V	400V
MB6S	MB6S	600V	420V	600V
MB8S	MB8S	800V	560V	800V
MB10S	MB10S	1000V	700V	1000V

## Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	0.8A	Note $T_A = 30^\circ\text{C}$
Peak Forward Surge Current	$I_{FSM}$	30A	8.3ms, half sine
Maximum Instantaneous Forward Voltage	$V_F$	1.0V	$I_{FM} = 0.5A;$ $T_A = 25^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Voltage	$I_R$	10 $\mu\text{A}$	$T_A = 25^\circ\text{C}$
Typical Junction Capacitance	$C_J$	25pF	Measured at 1.0MHz, $V_R=4.0V$

Note1. Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts

Note2. On alum: substrate P.C.B with an rea of 0.8 x 0.8 x 0.25"  
( 20 x 20 x 6.4mm ) mounte on 0.05 x 0.05 "( 13 x 13 mm )  
solder pad.

\*Pulse Test: Pulse Width 300 $\mu\text{sec}$ , Duty Cycle 1%

## 0.8Amp Single Phase Glass Passivated Bridge Rectifier 50 to 1000 Volts

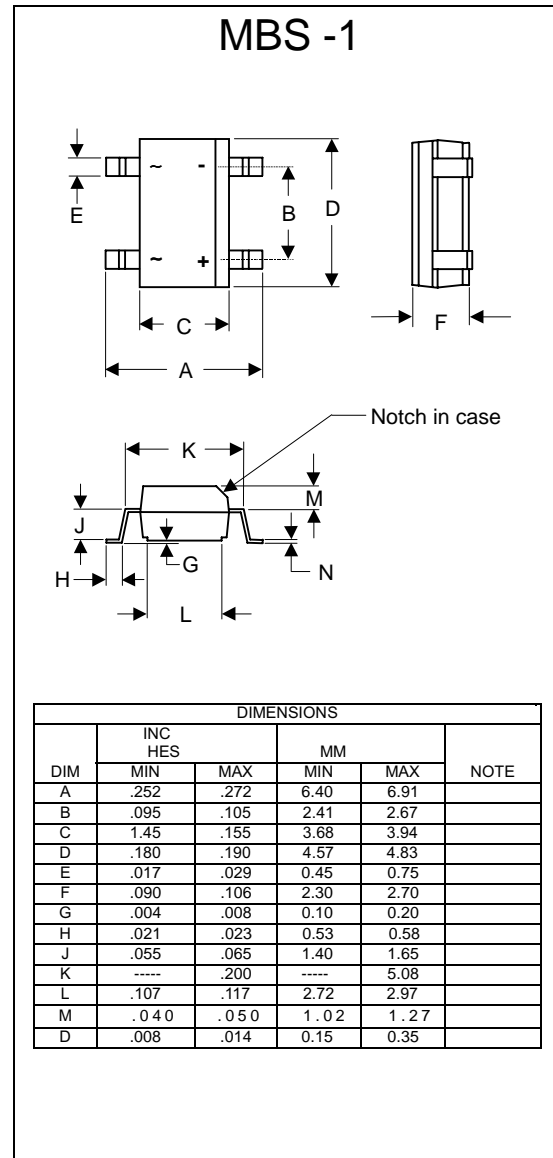
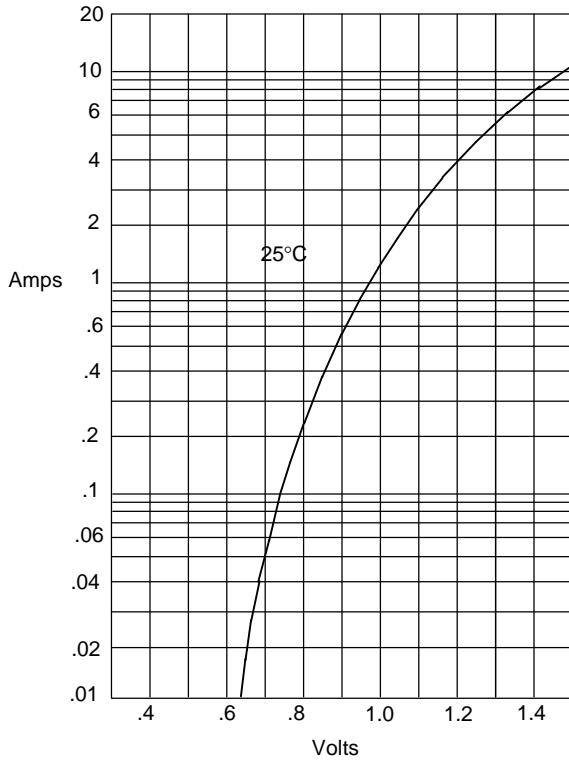
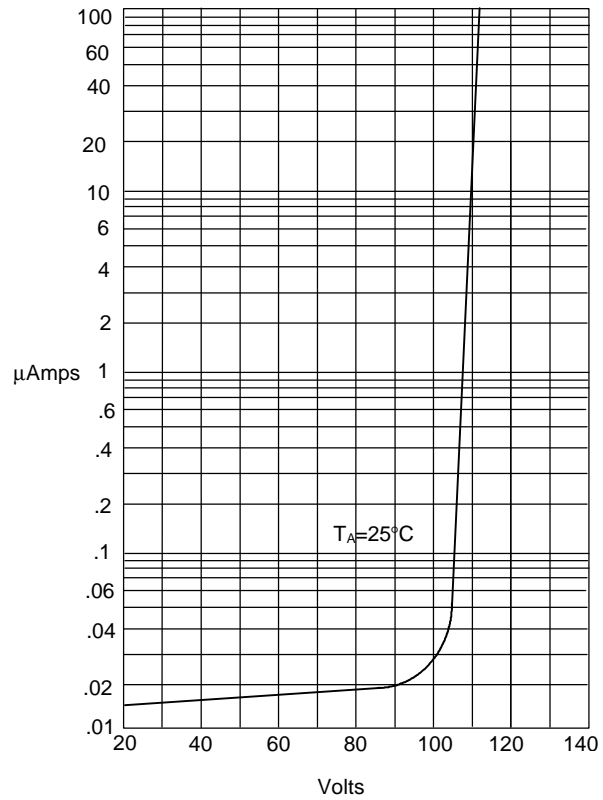


Figure 1  
Typical Forward Characteristics



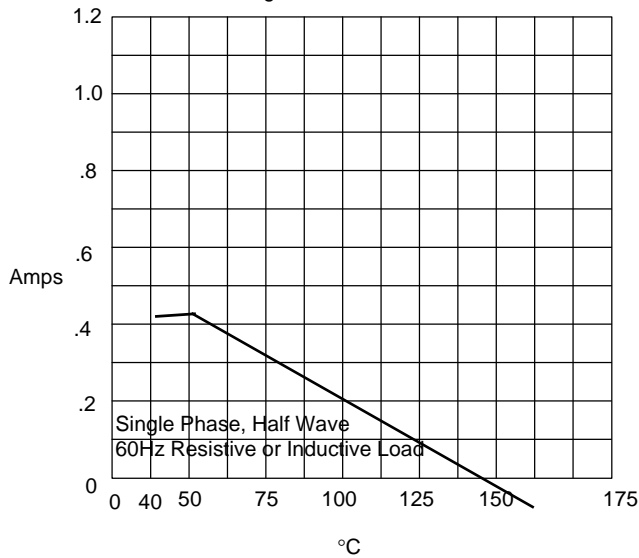
Instantaneous Forward Current - Amperes versus  
Instantaneous Forward Voltage - Volts

Figure 2  
Typical Reverse Characteristics



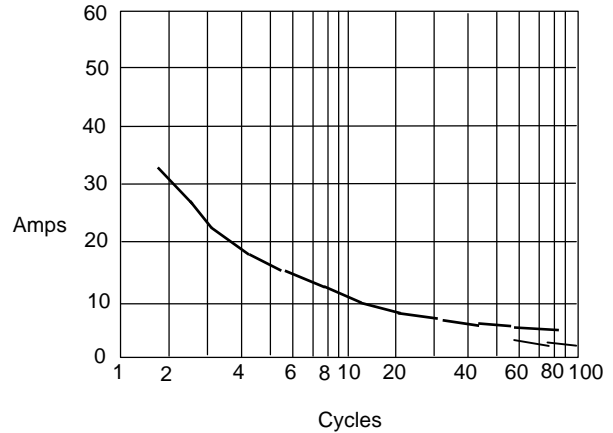
Instantaneous Reverse Leakage Current - MicroAmperes versus  
Percent Of Rated Peak Reverse Voltage - Volts

Figure 3  
Forward Derating Curve



Average Forward Rectified Current - Amperes versus  
Ambient Temperature - °C

Figure 4  
Peak Forward Surge Current



Peak Forward Surge Current - Amperes versus  
Number Of Cycles At 60Hz - Cycles

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)